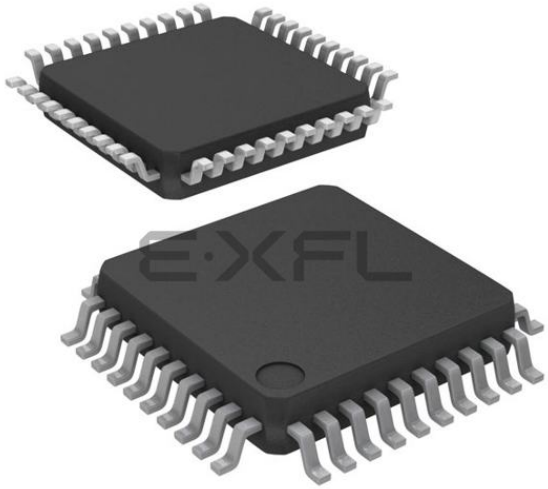
Renesas Electronics America Inc - R5F21262SNFP#X6 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21262snfp-x6

1. Overview

These MCUs are fabricated using a high-performance silicon gate CMOS process, embedding the R8C CPU core, and are packaged in a 32-pin molded-plastic LQFP. It implements sophisticated instructions for a high level of instruction efficiency. With 1 Mbyte of address space, they are capable of executing instructions at high speed.
Furthermore, the R8C/27 Group has on-chip data flash (1 KB × 2 blocks).
The difference between the R8C/26 Group and R8C/27 Group is only the presence or absence of data flash.
Their peripheral functions are the same.

1.1 Applications

Electronic household appliances, office equipment, audio equipment, consumer products, automotive, etc.

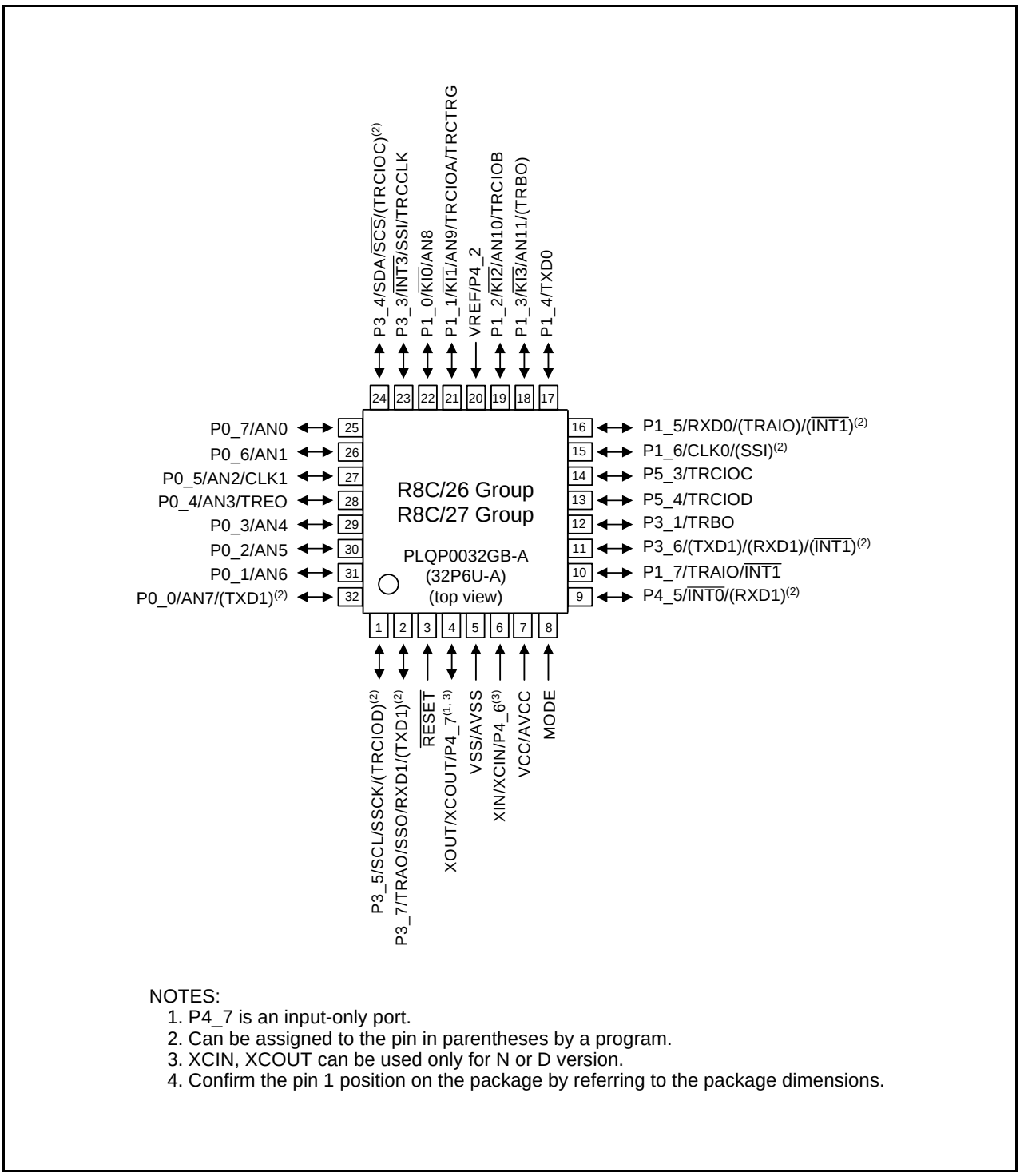
Table 1.2 Functions and Specifications for R8C/27 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) (other than K version) 62.5 ns (f(XIN) = 16 MHz, VCC = 3.0 to 5.5 V) (K version) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 2.2 to 5.5 V) (N, D version)
	Operating mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.4 Product Information of R8C/27 Group**
Peripheral Functions	Ports	I/O ports: 25 pins, Input port: 3 pins
	LED drive ports	I/O ports: 8 pins (N, D version)
	Timers	Timer RA: 8 bits × 1 channel Timer RB: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer RC: 16 bits × 1 channel (Input capture and output compare circuits) Timer RE: With real-time clock and compare match function (For J, K version, compare match function only.)
	Serial interfaces	2 channels (UART0, UART1) Clock synchronous serial I/O, UART
	Clock synchronous serial interface	1 channel I^2C bus Interface(1) Clock synchronous serial I/O with chip select
	LIN module	Hardware LIN: 1 channel (timer RA, UART0)
	A/D converter	10-bit A/D converter: 1 circuit, 12 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Start-on-reset selectable
	Interrupts	Internal: 15 sources, External: 4 sources, Software: 4 sources, Priority levels: 7 levels
	Clock generation circuits	3 circuits • XIN clock generation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has a frequency adjustment function • XCIN clock generation circuit (32 kHz) (N, D version) • Real-time clock (timer RE) (N, D version)
	Oscillation-stopped detector	XIN clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electrical Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) (other than K version) VCC = 3.0 to 5.5 V (f(XIN) = 16 MHz) (K version) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz) VCC = 2.2 to 5.5 V (f(XIN) = 5 MHz) (N, D version)
	Current consumption (N, D version)	Typ. 10 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 6 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 2.0 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	10,000 times (data flash)
		1,000 times (program ROM)
Operating Ambient Temperature		-20 to 85°C (N version)
		-40 to 85°C (D, J version)(2), -40 to 125°C (K version)(2)
Package		32-pin molded-plastic LQFP

NOTES:
1. I^2C bus is a trademark of Koninklijke Philips Electronics N. V.
2. Specify the D, K version if D, K version functions are to be used.

1.5 Pin Assignments

Figure 1.4 shows Pin Assignments (Top View).



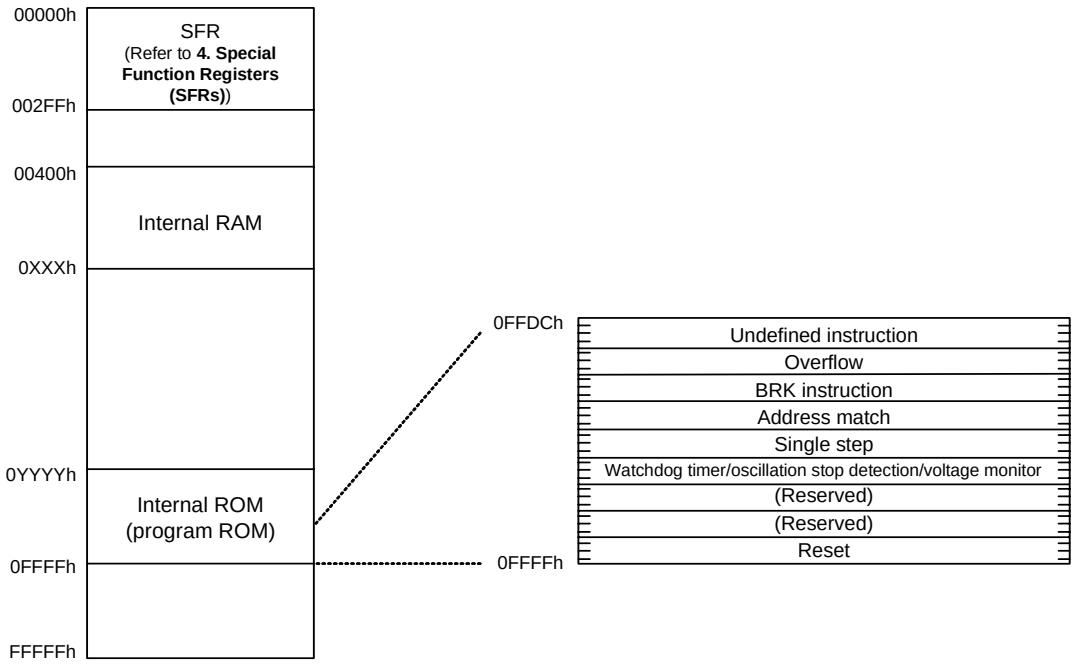
NOTES:
1. P4_7 is an input-only port.
2. Can be assigned to the pin in parentheses by a program.
3. XCIN, XCOUT can be used only for N or D version.
4. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.4 Pin Assignments (Top View)

3. Memory

3.1 R8C/26 Group

Figure 3.1 is a Memory Map of R8C/26 Group. The R8C/26 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



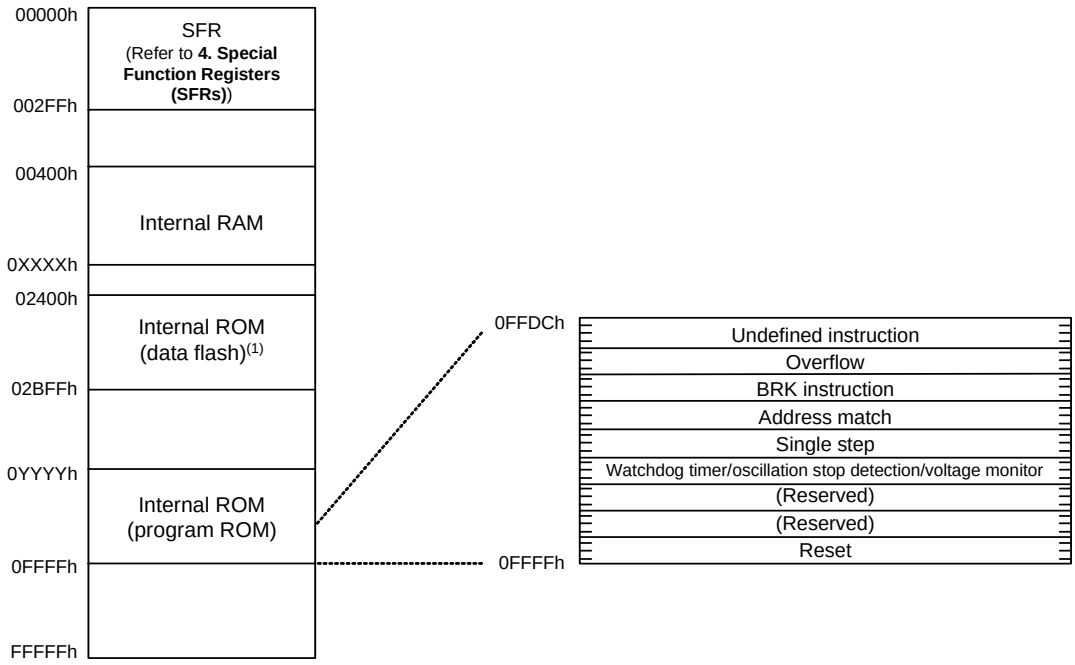
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F21262SNFP, R5F21262SDFP, R5F21262SNXXXFP, R5F21262SDXXXFP	8 Kbytes	0E000h	512 bytes	005FFh
R5F21264SNFP, R5F21264SDFP, R5F21264JFP, R5F21264KFP, R5F21264SNXXXFP, R5F21264SDXXXFP, R5F21264JXXXFP, R5F21264KXXXFP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21265SNFP, R5F21265SDFP R5F21265SNXXXFP, R5F21265SDXXXFP	24 Kbytes	0A000h	1.5 Kbytes	009FFh
R5F21266SNFP, R5F21266SDFP, R5F21266JFP, R5F21266KFP, R5F21266SNXXXFP, R5F21266SDXXXFP, R5F21266JXXXFP, R5F21266KXXXFP	32 Kbytes	08000h	1.5 Kbytes	009FFh

Figure 3.1 Memory Map of R8C/26 Group

3.2 R8C/27 Group

Figure 3.2 is a Memory Map of R8C/27 Group. The R8C/27 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F21272SNFP, R5F21272SDFP, R5F21272SNXXXFP, R5F21272SDXXXFP	8 Kbytes	0E000h	512 bytes	005FFh
R5F21274SNFP, R5F21274SDFP, R5F21274JFP, R5F21274KFP, R5F21274SNXXXFP, R5F21274SDXXXFP, R5F21274JXXXFP, R5F21274KXXXFP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21275SNFP, R5F21275SDFP, R5F21275SNXXXFP, R5F21275SDXXXFP	24 Kbytes	0A000h	1.5 Kbytes	009FFh
R5F21276SNFP, R5F21276SDFP, R5F21276JFP, R5F21276KFP, R5F21276SNXXXFP, R5F21276SDXXXFP, R5F21276JXXXFP, R5F21276KXXXFP	32 Kbytes	08000h	1.5 Kbytes	009FFh

Figure 3.2 Memory Map of R8C/27 Group

4. Special Function Registers (SFRs)

An SFR (special function register) is a control register for a peripheral function. Tables 4.1 to 4.7 list the special function registers.

Table 4.1 SFR Information (1)[1]

Address	Register	Symbol	After reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0	PM0	00h
0005h	Processor Mode Register 1	PM1	00h
0006h	System Clock Control Register 0	CM0	01101000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h			
0009h			
000Ah	Protect Register	PRCR	00h
000Bh			
000Ch	Oscillation Stop Detection Register	OCD	00000100b
000Dh	Watchdog Timer Reset Register	WDTR	XXh
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDC	00X11111b
0010h	Address Match Interrupt Register 0	RMAD0	00h
0011h			00h
0012h			00h
0013h	Address Match Interrupt Enable Register	AIER	00h
0014h	Address Match Interrupt Register 1	RMAD1	00h
0015h			00h
0016h			00h
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch	Count Source Protection Mode Register	CSPR	00h 10000000b[2]
001Dh			
001Eh			
001Fh			
0020h			
0021h			
0022h			
0023h	High-Speed On-Chip Oscillator Control Register 0	FRA0	00h
0024h	High-Speed On-Chip Oscillator Control Register 1	FRA1	When shipping
0025h	High-Speed On-Chip Oscillator Control Register 2	FRA2	00h
0026h			
0027h			
0028h	Clock Prescaler Reset Flag	CPSRF	00h
0029h	High-Speed On-Chip Oscillator Control Register 4[3]	FRA4	When shipping
002Ah			
002Bh	High-Speed On-Chip Oscillator Control Register 6[3]	FRA6	When shipping
002Ch	High-Speed On-Chip Oscillator Control Register 7[3]	FRA7	When shipping
002Dh			
002Eh			
002Fh			

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. The CSPROINI bit in the OFS register is set to 0.
3. In J, K version these regions are reserved. Do not access locations in these regions.

Table 4.6 SFR Information (6)[1]

Address	Register	Symbol	After reset
0140h			
0141h			
0142h			
0143h			
0144h			
0145h			
0146h			
0147h			
0148h			
0149h			
014Ah			
014Bh			
014Ch			
014Dh			
014Eh			
014Fh			
0150h			
0151h			
0152h			
0153h			
0154h			
0155h			
0156h			
0157h			
0158h			
0159h			
015Ah			
015Bh			
015Ch			
015Dh			
015Eh			
015Fh			
0160h			
0161h			
0162h			
0163h			
0164h			
0165h			
0166h			
0167h			
0168h			
0169h			
016Ah			
016Bh			
016Ch			
016Dh			
016Eh			
016Fh			
0170h			
0171h			
0172h			
0173h			
0174h			
0175h			
0176h			
0177h			
0178h			
0179h			
017Ah			
017Bh			
017Ch			
017Dh			
017Eh			
017Fh			

NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}	–	–	10	Bits
–	Absolute accuracy	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±3	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±2	LSB
		10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±5	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±2	LSB
		10-bit mode	ϕ_{AD} = 5 MHz, V_{ref} = AV_{CC} = 2.2 V	–	–	±5	LSB
		8-bit mode	ϕ_{AD} = 5 MHz, V_{ref} = AV_{CC} = 2.2 V	–	–	±2	LSB
R_{ladder}	Resistor ladder		V_{ref} = AV_{CC}	10	–	40	kΩ
t_{conv}	Conversion time	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	3.3	–	–	µs
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	2.8	–	–	µs
V_{ref}	Reference voltage			2.2	–	AV_{CC}	V
V_{IA}	Analog input voltage(2)			0	–	AV_{CC}	V
–	A/D operating clock frequency	Without sample and hold	V_{ref} = AV_{CC} = 2.7 to 5.5 V	0.25	–	10	MHz
		With sample and hold	V_{ref} = AV_{CC} = 2.7 to 5.5 V	1	–	10	MHz
		Without sample and hold	V_{ref} = AV_{CC} = 2.2 to 5.5 V	0.25	–	5	MHz
		With sample and hold	V_{ref} = AV_{CC} = 2.2 to 5.5 V	1	–	5	MHz

NOTES:
1. AV_{CC} = 2.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

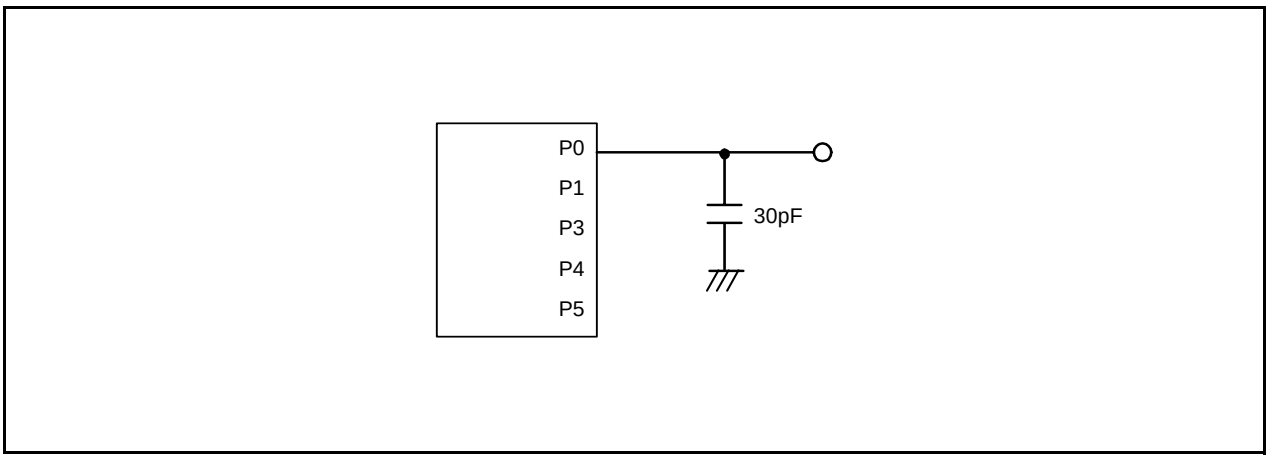


Figure 5.1 Ports P0, P1, and P3 to P5 Timing Measurement Circuit

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		-20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. -40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	V_{CC} = 4.75 to 5.25 V 0°C ≤ T_{opr} ≤ 60°C(2)	39.2	40	40.8	MHz
		V_{CC} = 3.0 to 5.5 V -20°C ≤ T_{opr} ≤ 85°C(2)	38.8	40	41.2	MHz
		V_{CC} = 3.0 to 5.5 V -40°C ≤ T_{opr} ≤ 85°C(2)	38.4	40	41.6	MHz
		V_{CC} = 2.7 to 5.5 V -20°C ≤ T_{opr} ≤ 85°C(2)	38	40	42	MHz
		V_{CC} = 2.7 to 5.5 V -40°C ≤ T_{opr} ≤ 85°C(2)	37.6	40	42.4	MHz
		V_{CC} = 2.2 to 5.5 V -20°C ≤ T_{opr} ≤ 85°C(3)	35.2	40	44.8	MHz
		V_{CC} = 2.2 to 5.5 V -40°C ≤ T_{opr} ≤ 85°C(3)	34	40	46	MHz
		V_{CC} = 5.0 V ± 10% -20°C ≤ T_{opr} ≤ 85°C(2)	38.8	40	40.8	MHz
		V_{CC} = 5.0 V ± 10% -40°C ≤ T_{opr} ≤ 85°C(2)	38.4	40	40.8	MHz
	High-speed on-chip oscillator frequency when correction value in FRA7 register is written to FRA1 register(4)	V_{CC} = 5.0 V, T_{opr} = 25°C	–	36.864	–	MHz
		V_{CC} = 3.0 to 5.5 V -20°C ≤ T_{opr} ≤ 85°C	-3%	–	3%	%
–	Value in FRA1 register after reset		08h(3)	–	F7h(3)	–
–	Oscillation frequency adjustment unit of high-speed on-chip oscillator	Adjust FRA1 register (value after reset) to -1	–	+0.3	–	MHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	400	–	µA

NOTES:
1. V_{CC} = 2.2 to 5.5 V, T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. These standard values show when the FRA1 register value after reset is assumed.
3. These standard values show when the corrected value of the FRA6 register is written to the FRA1 register.
4. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.11 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		30	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	15	–	µA

NOTE:
1. V_{CC} = 2.2 to 5.5 V, T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.

Table 5.12 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until system clock supply starts after the interrupt is acknowledged to exit stop mode.

Table 5.22 Electrical Characteristics (3) [V_{CC} = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P1_0 to P1_7, XOUT	I_{OH} = -1 mA		V_{CC} - 0.5	–	V_{CC}	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OH} = -5 mA	V_{CC} - 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -1 mA	V_{CC} - 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	V_{CC} - 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -50 µA	V_{CC} - 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P1_0 to P1_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3 V		–	–	-4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3 V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. V_{CC} = 2.7 to 3.3 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.29 Electrical Characteristics (6) [Vcc = 2.2 V]
(T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 2.2 to 2.7 V) Single-chip mode, output pins are open, other pins are V_{SS}	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	100	230	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	100	230	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	25	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	22	60	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	20	55	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.0	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	1.8	–	µA
		Stop mode	XIN clock off, T_{opr} = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	µA
			XIN clock off, T_{opr} = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.1	–	µA

Table 5.37 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/26 Group	100(3)	–	–	times
		R8C/27 Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

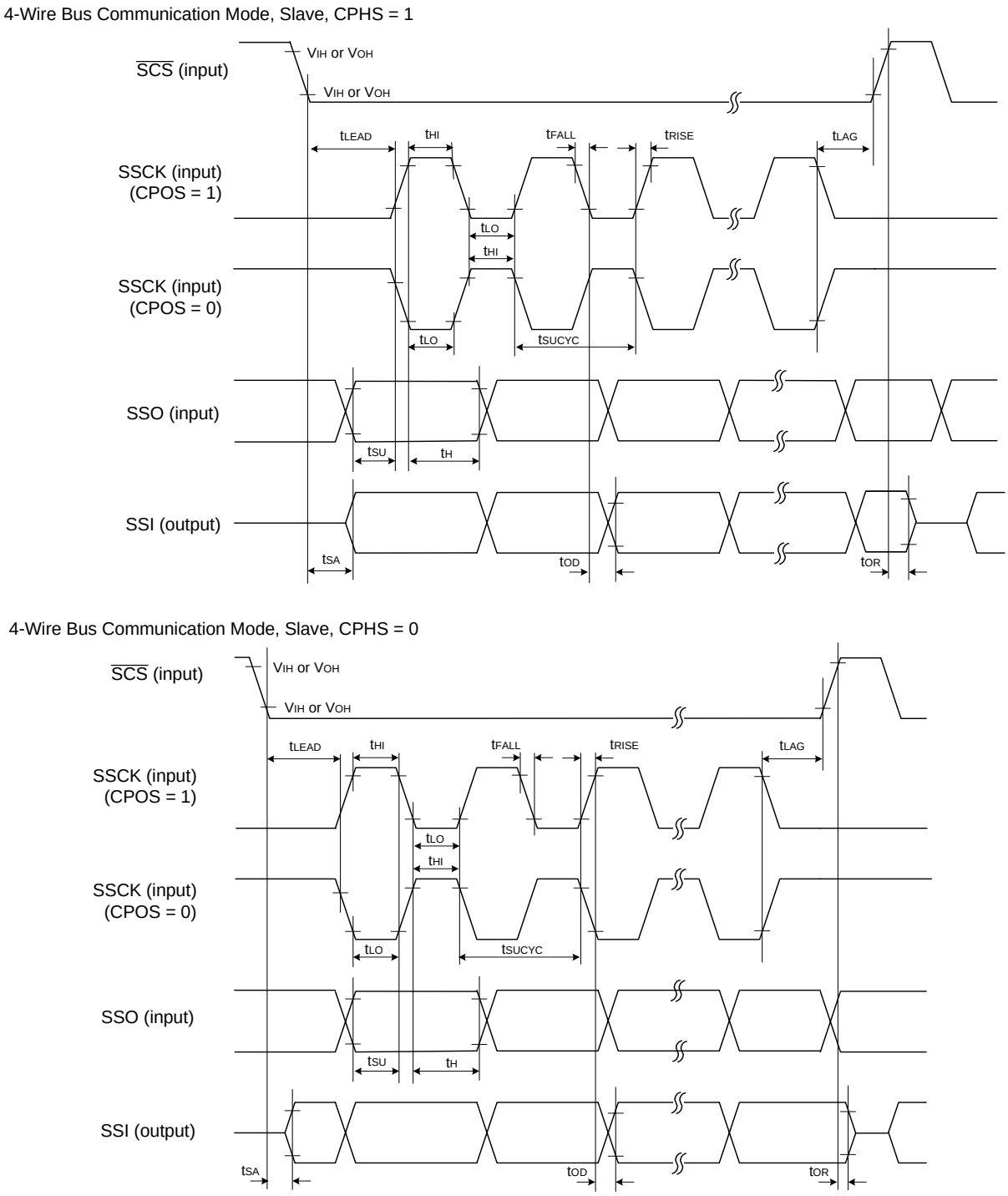


Figure 5.24 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

Table 5.46 Timing Requirements of I²C bus Interface(1)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{SCL}	SCL input cycle time		$12t_{CYC} + 600$(2)	–	–	ns
t_{SCLH}	SCL input “H” width		$3t_{CYC} + 300$(2)	–	–	ns
t_{SCLL}	SCL input “L” width		$5t_{CYC} + 500$(2)	–	–	ns
t_{sf}	SCL, SDA input fall time		–	–	300	ns
t_{SP}	SCL, SDA input spike pulse rejection time		–	–	$1t_{CYC}$(2)	ns
t_{BUF}	SDA input bus-free time		$5t_{CYC}$(2)	–	–	ns
t_{STAH}	Start condition input hold time		$3t_{CYC}$(2)	–	–	ns
t_{STAS}	Retransmit start condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{STOP}	Stop condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{SDAS}	Data input setup time		$1t_{CYC} + 20$(2)	–	–	ns
t_{SDAH}	Data input hold time		0	–	–	ns

NOTES:
1. V_{CC} = 2.7 to 5.5 V, V_{SS} = 0 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. $1t_{CYC} = 1/f1(s)$

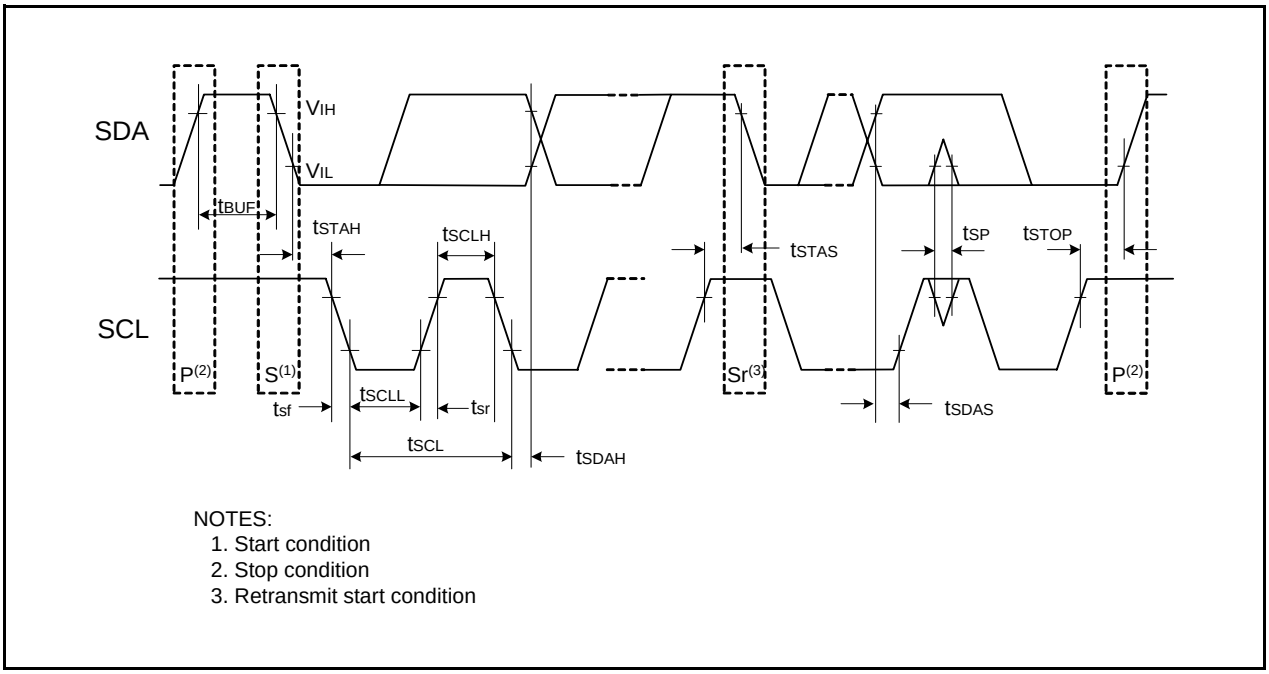


Figure 5.26 I/O Timing of I²C bus Interface

Table 5.47 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except XOUT	I_{OH} = -5 mA		V_{CC} - 2.0	–	V_{CC}	V
			I_{OH} = -200 μA		V_{CC} - 0.3	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 μA	V_{CC} - 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 μA		–	–	0.45	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 μA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5V		–	–	-5.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.53 Electrical Characteristics (3) [V_{CC} = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except XOUT	I_{OH} = -1 mA		V_{CC} - 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	V_{CC} - 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -50 µA	V_{CC} - 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except XOUT	I_{OL} = 1 mA		–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0,CLK1, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3V		–	–	-4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:
1. V_{CC} = 2.7 to 3.3 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 10 MHz, unless otherwise specified.

Timing requirements
(Unless Otherwise Specified: V_{CC} = 3 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 3 V]

Table 5.55 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	100	–	ns
$t_{WH(XIN)}$	XIN input “H” width	40	–	ns
$t_{WL(XIN)}$	XIN input “L” width	40	–	ns

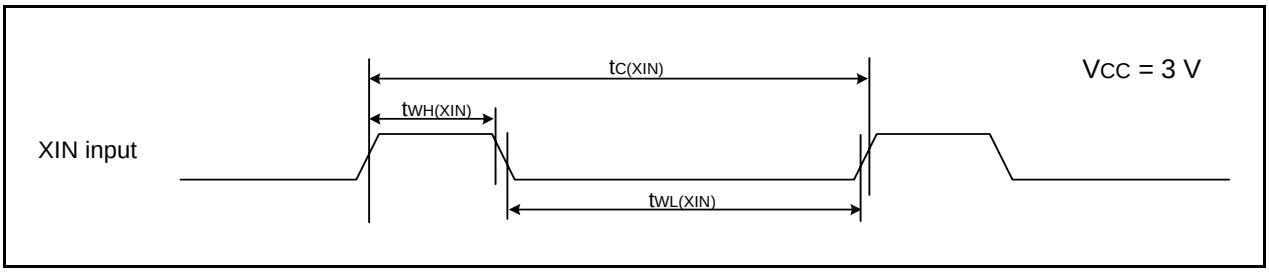


Figure 5.31 XIN Input Timing Diagram when V_{CC} = 3 V

Table 5.56 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	–	ns

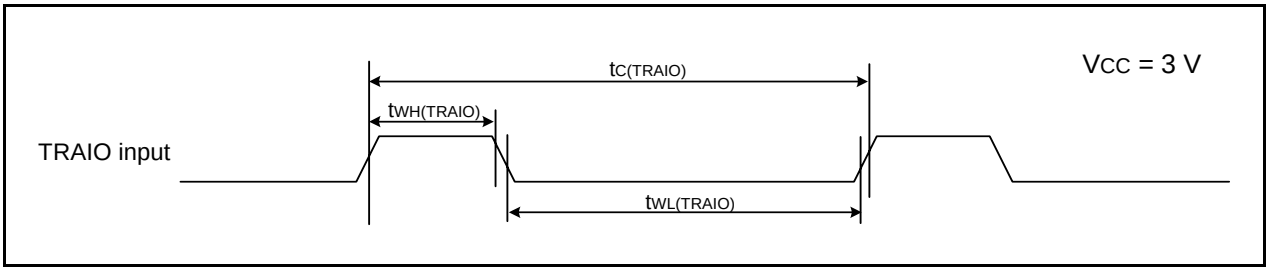


Figure 5.32 TRAIO Input Timing Diagram when V_{CC} = 3 V

REVISION HISTORY	R8C/26 Group, R8C/27 Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Nov 08, 2006	27	Table 5.9, Figure 5.3 revised and Table 5.10 deleted
		28	Table 5.10, Table 5.11 revised
		34	Table 5.15 revised
		35	Table 5.16 revised
		36	Table 5.17 revised
		39	Table 5.22 revised
		40	Table 5.23 revised
		44	Table 5.29 revised
		47	Package Dimensions; “Diagrams showing the latest...website.” added
1.10	Nov 29, 2006	All pages	“J, K version” added
		1	1 “J and K versions are under development...notice.” added 1.1 revised
		2	Table 1.1 revised
		3	Table 1.2 revised
		4	Figure 1.1 NOTE3 added
		5	Table 1.3, Figure 1.2 revised
		6	Table 1.4, Figure 1.3 revised
		7	Figure 1.4 NOTE3 added
		8	Table 1.5 revised
		9	Table 1.6 NOTE2 added
		13	Figure 3.1 revised
		14	Figure 3.2 revised
		15	Table 4.1; “0000h to 003Fh” → “0000h to 002Fh” revised • NOTE3 added
		16	Table 4.2; “0040h to 007Fh” → “0030h to 007Fh” revised • 0032h, 0036h: “After reset” is revised • 0038h: NOTE revised • NOTES 2, 5, 6 revised and NOTE 7, 8 added
		19	Table 4.5 NOTE2 added
		28	Table 5.10 revised
		48 to 66	5.2 J, K Version added
1.20	Jan 17, 2007	18	Table 4.4 NOTE2 added
1.30	May 25, 2007	2	Table 1.1 revised
		3	Table 1.2 revised
		5	Table 1.3 revised
		6	Figure 1.2 revised
		7	Table 1.4 revised
		8	Figure 1.3 revised
		9	Figure 1.4 NOTE4 added
		15	Figure 3.1 part number revised

REVISION HISTORY	R8C/26 Group, R8C/27 Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.30	May 25, 2007	16	Figure 3.2 part number revised
		30	Table 5.10 revised
		53	Table 5.39 NOTE4 added
		55	Table 5.42 revised
1.40a	Jun 14, 2007	5, 7	Table 1.3 and Table 1.4 revised
2.00	Mar 01, 2008	1, 49	1.1, 5.2 “J and K versions are ...” deleted
		5, 7	Table 1.3, Table 1.4 revised
		11	Table 1.6 NOTE3 added
		15, 16	Figure 3.1, Figure 3.2; “Expanded area” deleted
		17	Table 4.1 “002Ch” added
		18	Table 4.2 “0036h”; J, K version “0100X000b” → “0100X001b”
		24, 49	Table 5.2, Table 5.35; NOTE2 revised
		30	Table 5.10 revised, NOTE4 added
2.10	Sep 26, 2008	–	“RENESAS TECHNICAL UP DATE” reflected: TN-16C-A172A/E
		26, 51	Table 5.4, Table 5.37 NOTE2, NOTE4 revised
		27, 52	Table 5.5, Table 5.38 NOTE2, NOTE5 revised
		53	Table 5.39 Parameter: Voltage monitor 1 reset generation time added NOTE5 added Table 5.40 revised
		54	Table 5.41 revised Figure 5.22 revised

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